Electrical Characteristics of the IGBT T_j= 25 unless otherwise specified

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						
Collector-Emitter Breakdown Voltage	BV_{CES}	V_{GE}=0V, I_C	650		-	V
Gate Threshold Voltage	$V_{GE(th)}$	V_{GE}=V_{CE}, I_C=1mA	5.0	5.8	6.5	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	V_{GE}=15V, I_C=20A T_j=25°C, T_j=125°C T_j=150°C		1.60 1.75 1.80	1.95	V
Zero Gate Voltage Collector Current	I_{CES}	V_{CE}=600V, V_{GE}=0V T_j= 25°C, T_j=150°C			0.25 1.00	mA
Gate-Emitter Leakage Current	I_{GES}	V_{CE}= 0V, V_{GE}= ± 20V			±200	nA

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic						
Input Capacitance	C_{ies}	V				

Electrical

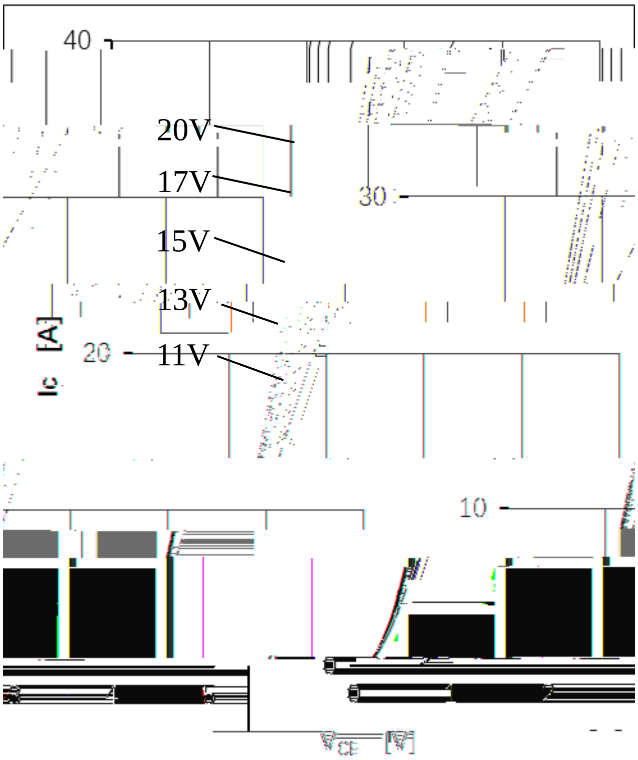


Fig1.IGBT Output Characteristics(25℃)

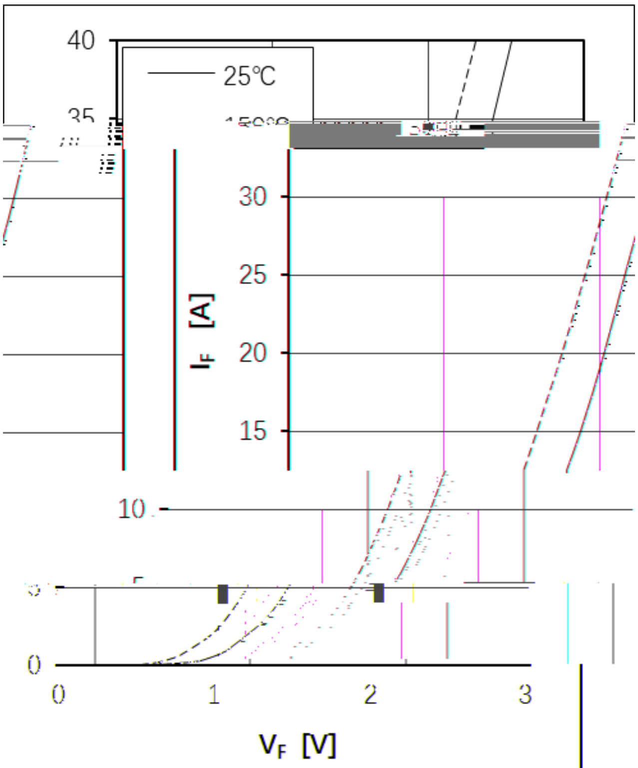
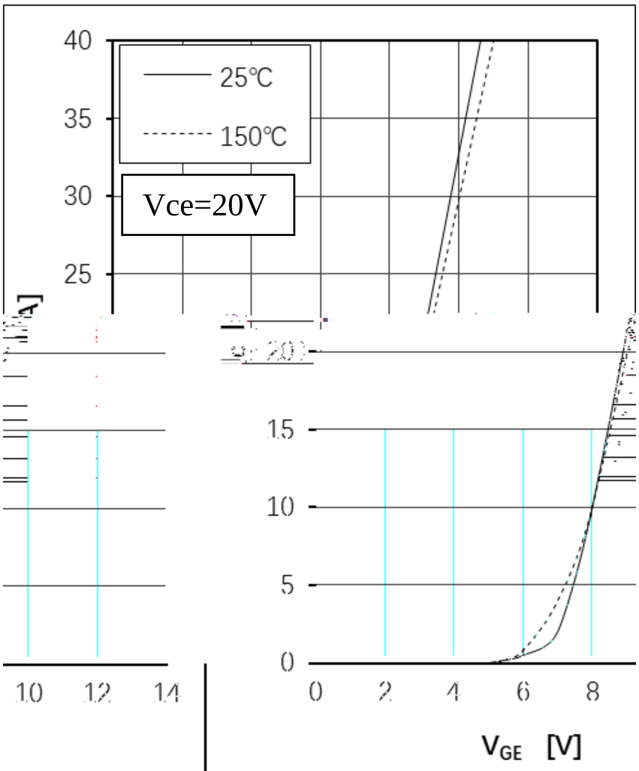


Fig3.Diode Foward Characteristics



eristics

Fig4.IGBT Transfer Charact

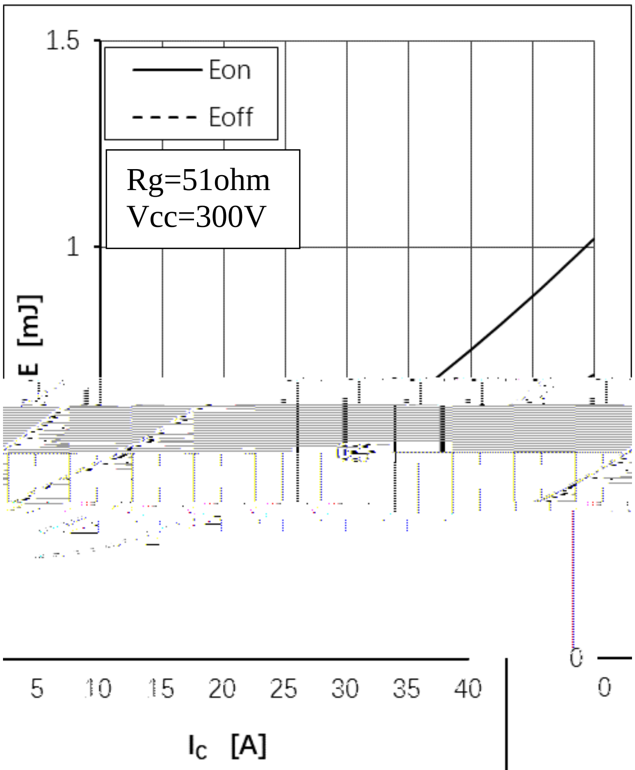
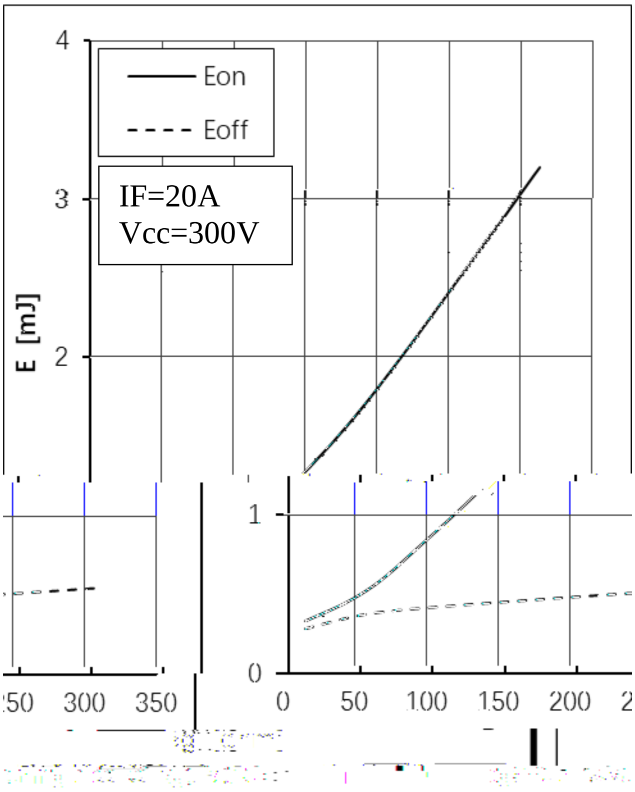
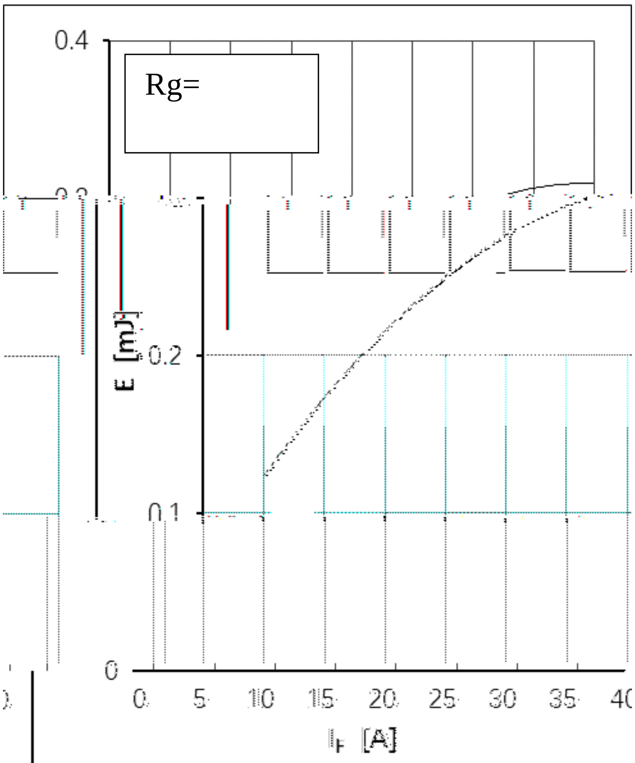
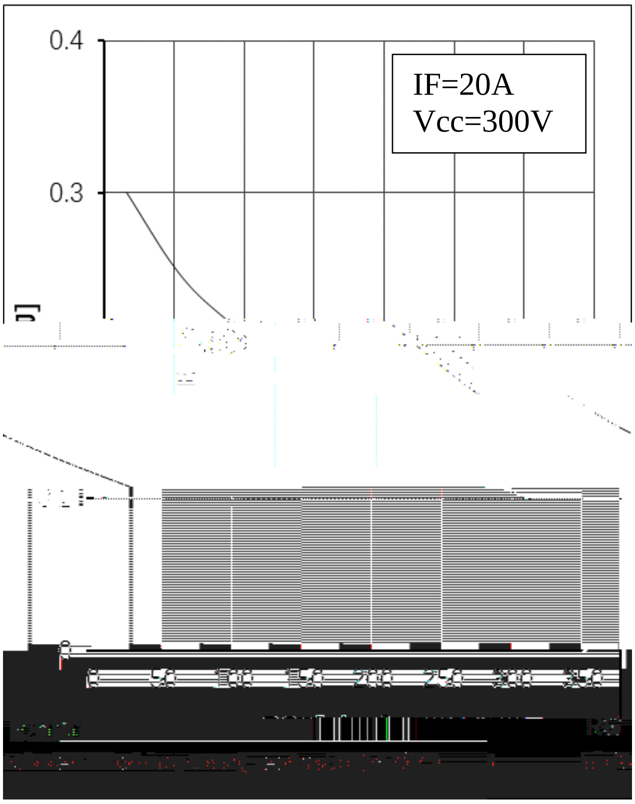
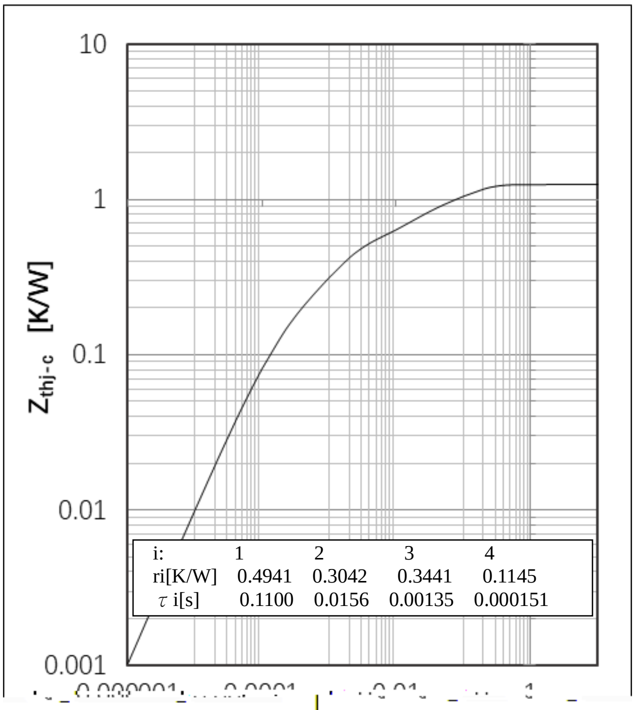


Fig5.IGBT Switching Loss vs.Ic(150℃)



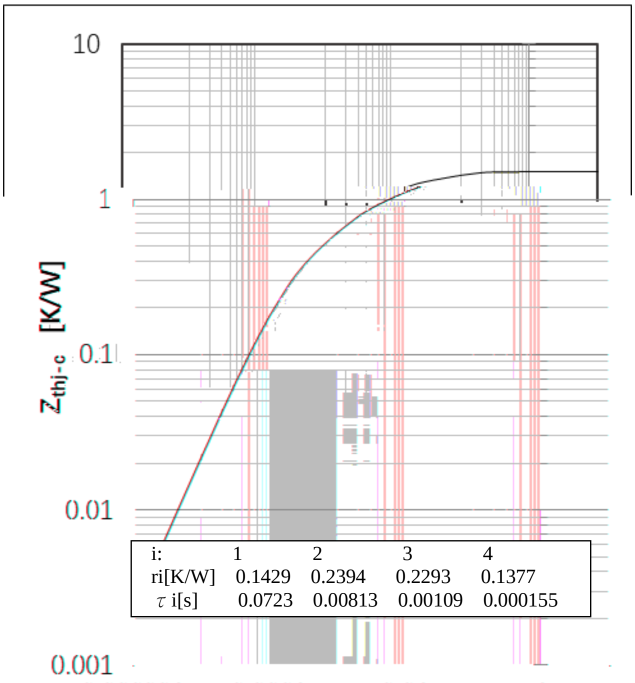






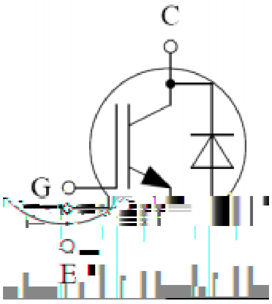
i:	1	2	3	4
ri[K/W]	0.4941	0.3042	0.3441	0.1145
τ i[s]	0.1100	0.0156	0.00135	0.000151

[illegible]



i:	1	2	3	4
ri[K/W]	0.1429	0.2394	0.2293	0.1377
τ i[s]	0.0723	0.00813	0.00109	0.000155

[redacted]



Package Outline Information

TO-247AB		
Dim	Min	M